Semiconductors

Resistors (all ¼-watt, ± 5% Carbon)		IC1 = NE555 (Timer IC)
		IC2 = LM741 (Operational Amplifier)
R1 = 250 Ω	Capacitors	IC3 = LM386 (Low power audio power amplifier)
R2 = 750 Ω		IC4, IC5 = PF08109B (Power Amplifier Module for E-GSM and DCS1800)
R3, R4, R6= 2 KΩ	C1, C3 – C7, C9 = 0.1 μ F (Ceramic Disc)	IC6 = CVCO55CL (Voltage Controlled Oscillator, 925-970MHZ)
R5 = 100 KΩ	C2, C15, C16 = 1nF (Ceramic Disc)	IC7 = CVCO55BE (Voltage Controlled Oscillator, 1785-1900MHZ)
R7 = 10 Ω	C8, C10 = 10 μ F, 16V (Electrolytic Capacitor)	T1 = 2N3904 (Smaller Signal Bipolar Junction Transistor)
R8, R9 = 1 KΩ	C11, C13 = 4.7 μ F, 16V (Electrolytic Capacitor) ZD1 = 6.8V Zener Diode	
R10 = 2 KΩ	C12, C14 = 0.01 µ (Ceramic Disc)	D1, D2 = 1N4148 (silicon switching signal diode)

Miscellaneous

Antenna 1 = GSM antenna (Frequency = 850MHz-1GHz, Input Impedance = 50Ω , VSWR<2)

Antenna 2 = DCS antenna (Frequency = 1700MHz-1900MHz, Input Impedance = 50Ω , VSWR<2)